

Product Summary

BV _{DSS}	R _{DS(ON)} MAX	I _D MAX T _A = +25°C
-60V	55mΩ @ V _{GS} = -10V	-10.4A
	80mΩ @ V _{GS} = -4.5V	-9.2A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Disconnect Switches
- Motor Control

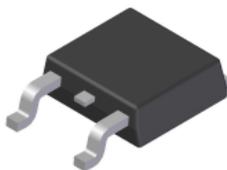
Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <https://www.diodes.com/quality/product-definitions/>**

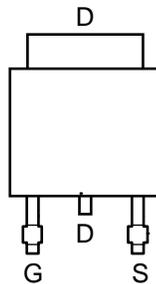
Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ^③
- Weight: 0.33 grams (Approximate)

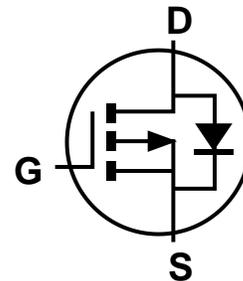
TO252 (DPAK)



Top View



Top View
Pin-Out



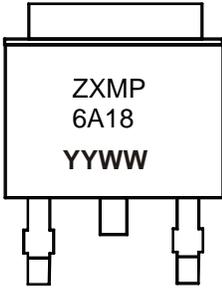
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
ZXMP6A18KTC	TO252 (DPAK)	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



ZXMP6A18 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 20 = 2020)
 WW = Week (01 to 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	-60	V
Gate-Source Voltage		V_{GSS}	± 20	V
Continuous Drain Current, $V_{GS} = -10\text{V}$	$T_A = +25^\circ\text{C}$ (Note 6)	I_D	-10.4	A
	$T_A = +70^\circ\text{C}$ (Note 6)		-8.3	
	$T_A = +25^\circ\text{C}$ (Note 5)		-6.8	
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%) (Note 7)		I_{DM}	-37.5	A
Maximum Body Diode Forward Current (Note 6)		I_S	-10.4	A
Pulsed Source Current (10 μs Pulse, Duty Cycle = 1%) (Note 7)		I_{SM}	-37.5	A
Avalanche Current, $L = 0.1\text{mH}$		I_{AS}	-36	A
Avalanche Energy, $L = 0.1\text{mH}$		E_{AS}	65	mJ

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

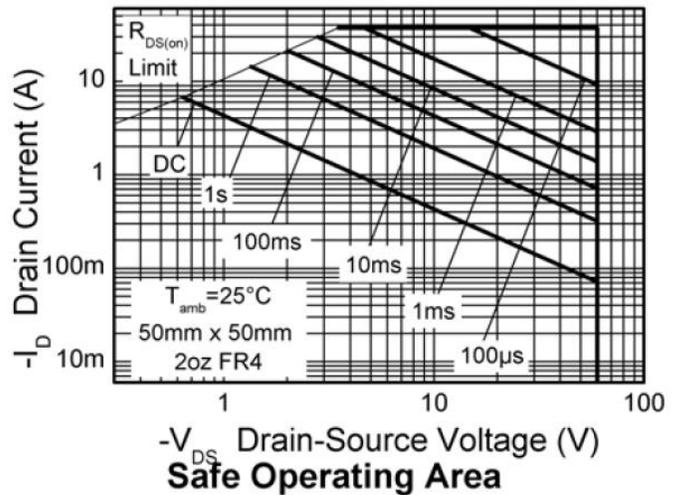
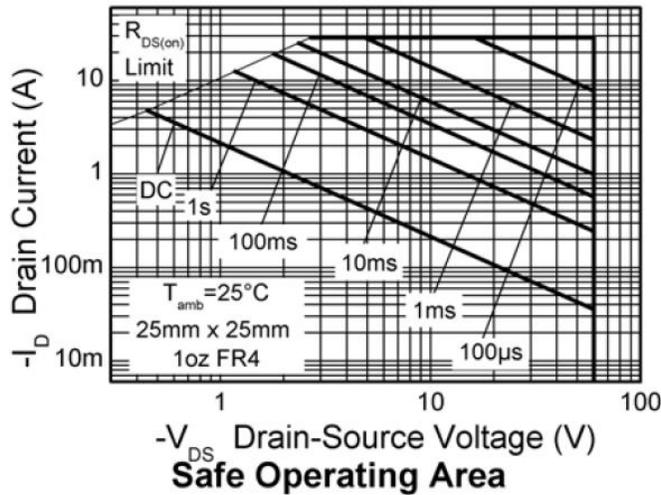
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	4.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	29	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)		P_D	10.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	12.3	$^\circ\text{C/W}$
Total Power Dissipation (Note 8)		P_D	2.15	W
Thermal Resistance, Junction to Case (Note 8)	Steady State	$R_{\theta JA}$	58	$^\circ\text{C/W}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

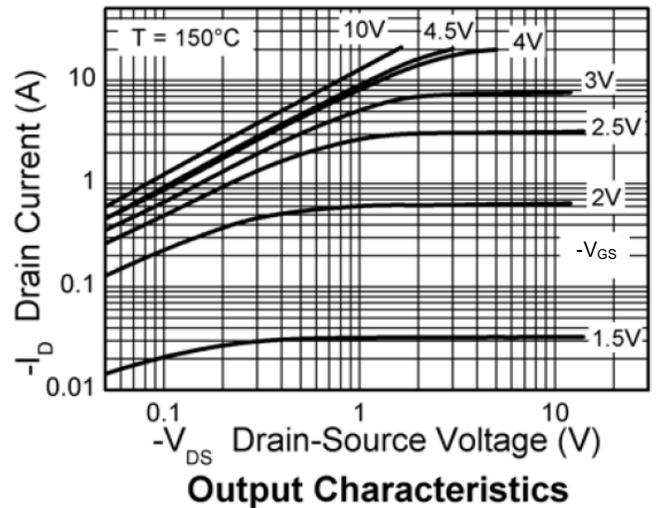
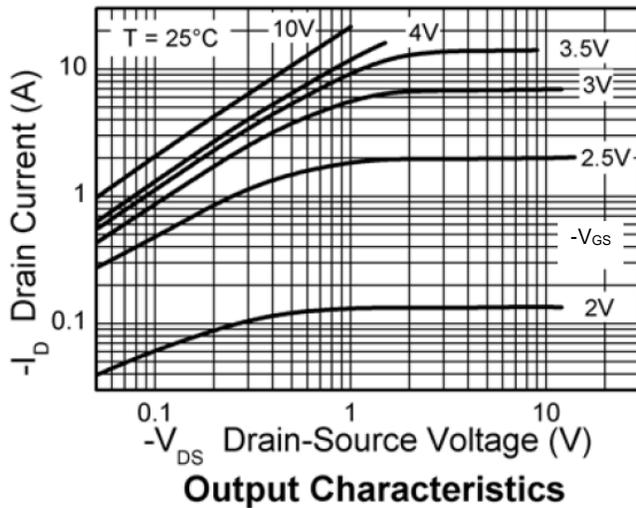
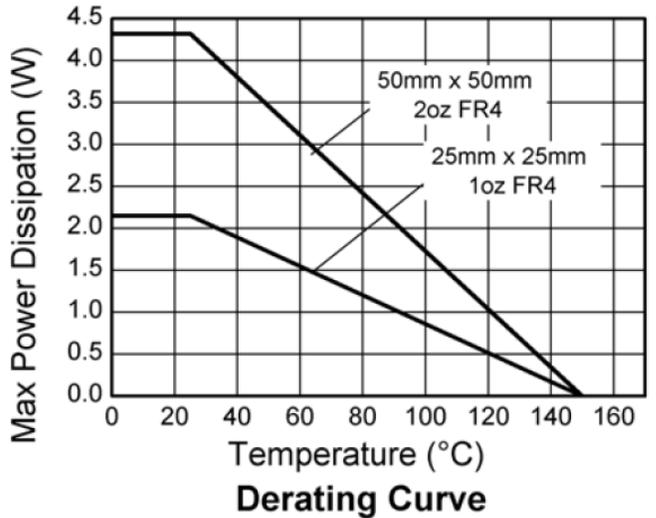
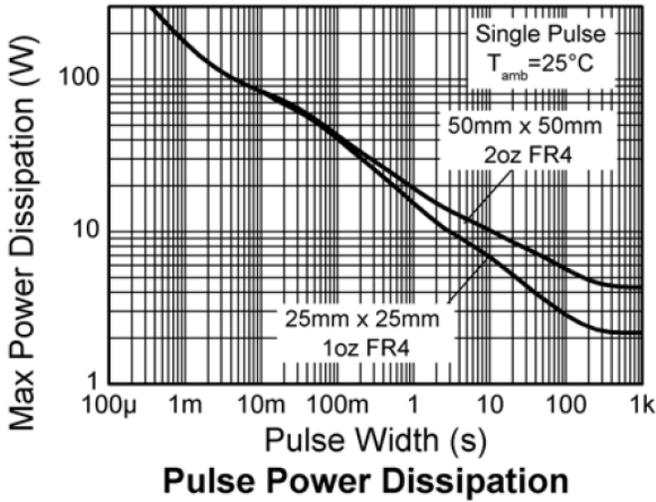
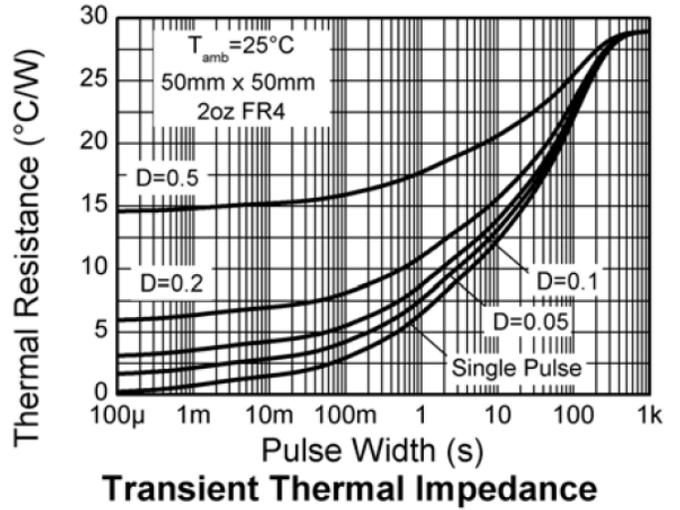
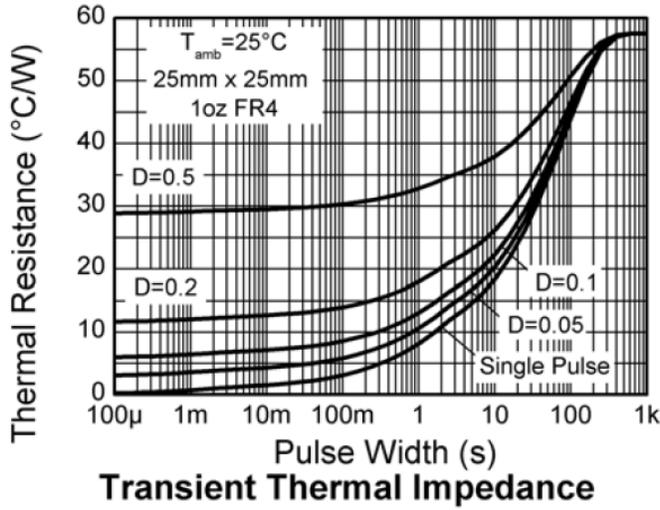
- Notes:
5. For a device surface mounted on 50mm x 50mm x 1.6mm FR-4 PCB with high coverage of single sided 2oz copper, in still air conditions.
 6. For a device surface mounted on FR-4 PCB measured at $t \leq 10\text{s}$.
 7. Repetitive rating 50mm x 50mm x 1.6mm FR-4 PCB, $D=0.02$ pulse width=300s - pulse width limited by maximum junction temperature.
 8. For a device surface mounted on 25mm x 25mm x 1.6mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.

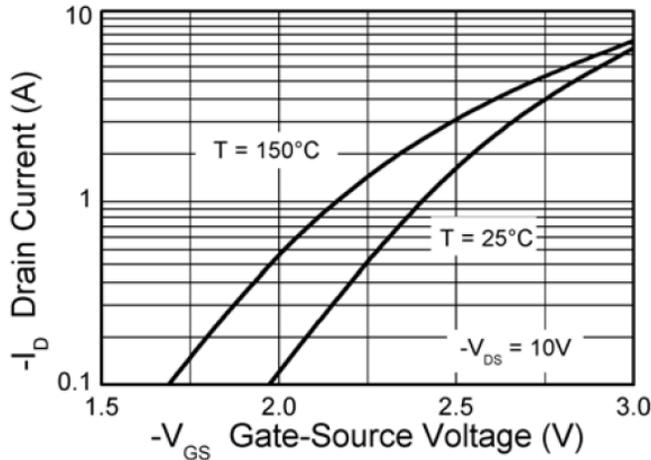
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	-1.0	—	—	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	44	55	mΩ	V _{GS} = -10V, I _D = -3.5A
		—	59	80		V _{GS} = -4.5V, I _D = -2.9A
Forward Transconductance	g _{fs}	—	8.7	—	s	V _{DS} = -15V, I _D = -3.5A
Diode Forward Voltage	V _{SD}	—	-0.85	-0.95	V	V _{GS} = 0V, I _S = -4.2A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	1580	—	pF	V _{DS} = -30V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	160	—		
Reverse Transfer Capacitance	C _{rss}	—	140	—		
Total Gate Charge (V _{GS} = -5V)	Q _G	—	23	—	nC	V _{DS} = -30V, I _D = -3.5A
Total Gate Charge (V _{GS} = -10V)	Q _G	—	44	—		
Gate-Source Charge	Q _{GS}	—	3.9	—		
Gate-Drain Charge	Q _{GD}	—	9.8	—		
Turn-On Delay Time	t _{D(ON)}	—	4.6	—	ns	V _{GS} = -10V, V _{DD} = -30V, R _G = 6Ω, I _D = -1A
Turn-On Rise Time	t _r	—	5.8	—		
Turn-Off Delay Time	t _{D(OFF)}	—	55	—		
Turn-Off Fall Time	t _f	—	23	—		
Reverse Recovery Time	t _{RR}	—	37	—	ns	I _S = -2.1A, di/dt = -100A/μs
Reverse Recovery Charge	Q _{RR}	—	56	—	nC	I _S = -2.1A, di/dt = -100A/μs

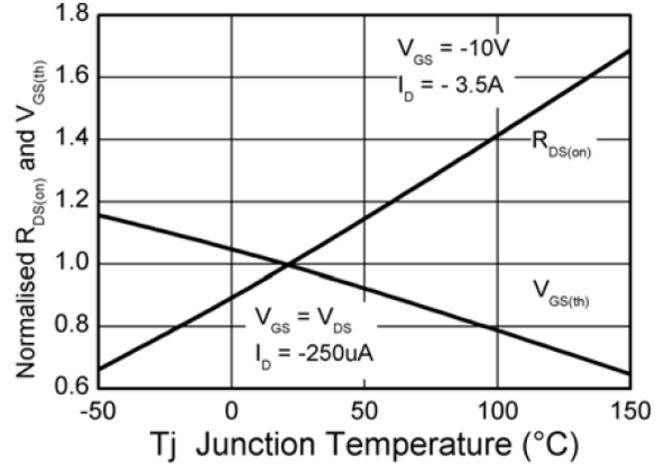
Notes: 9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.



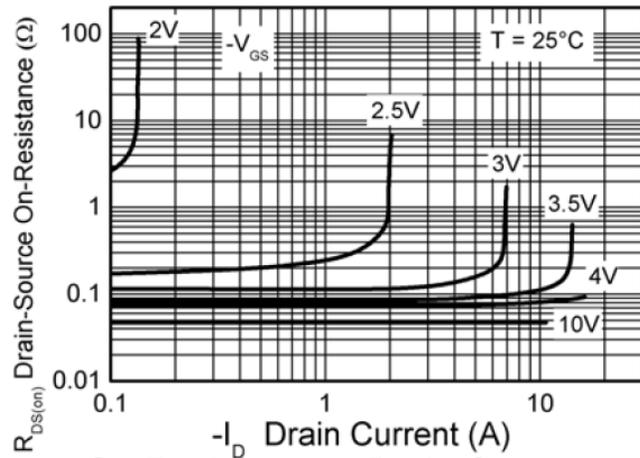




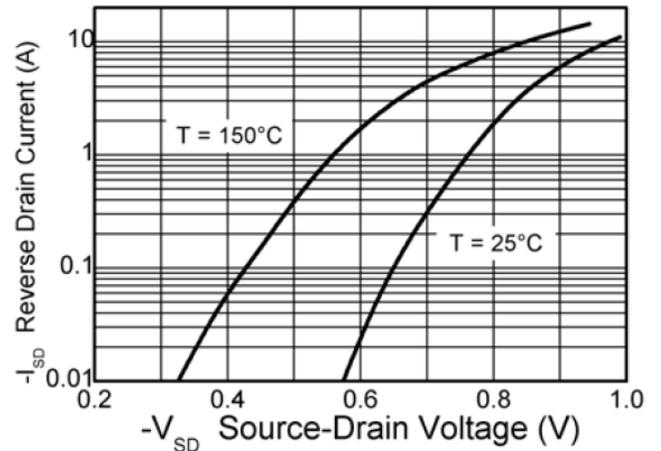
Typical Transfer Characteristics



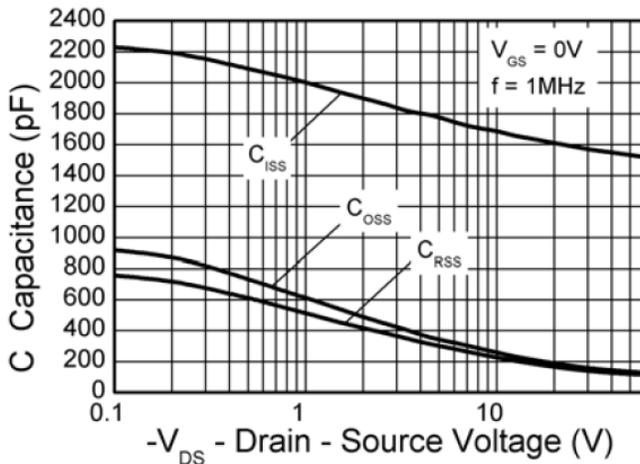
Normalised Curves v Temperature



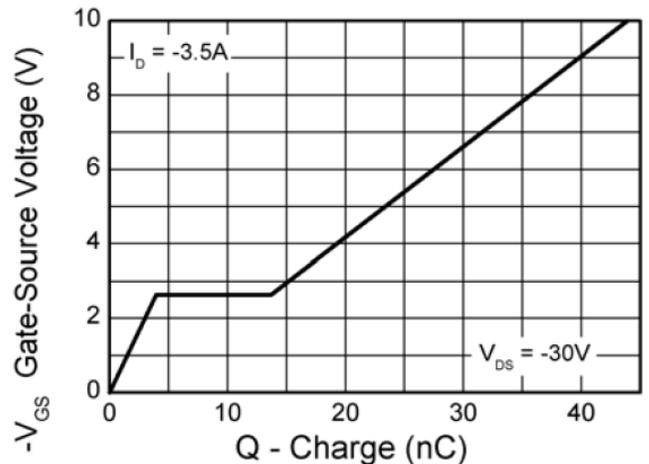
On-Resistance v Drain Current



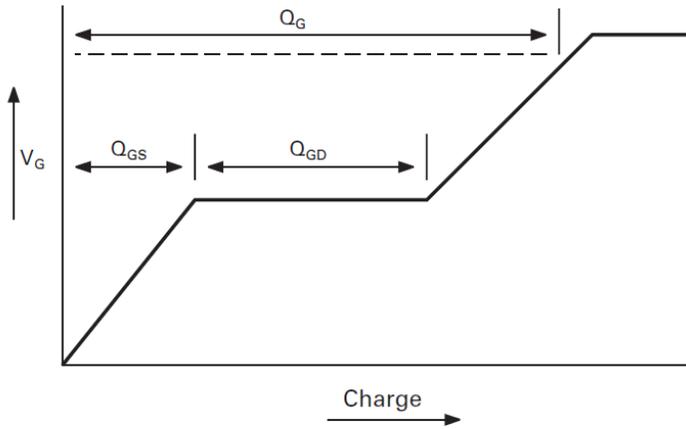
Source-Drain Diode Forward Voltage



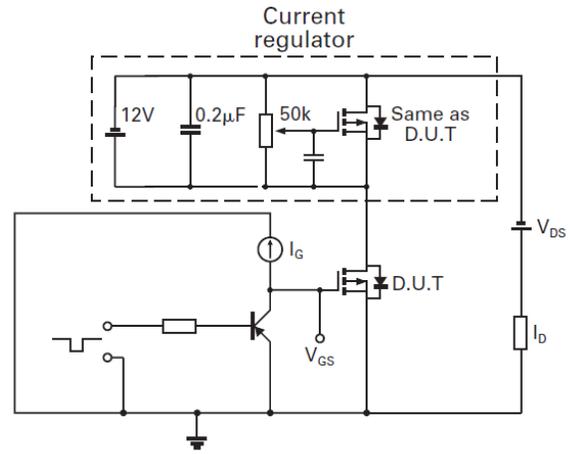
Capacitance v Drain-Source Voltage



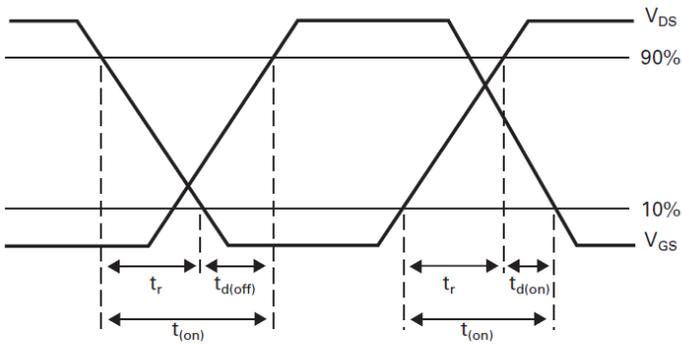
Gate-Source Voltage v Gate Charge



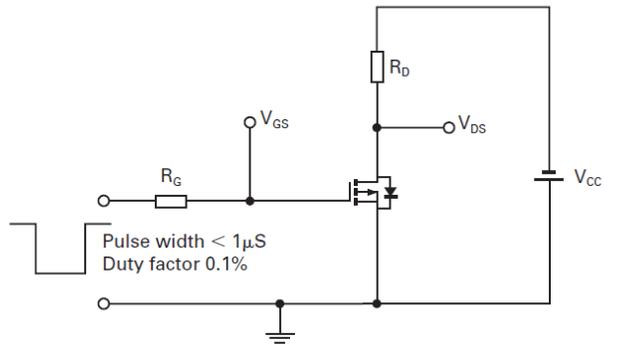
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

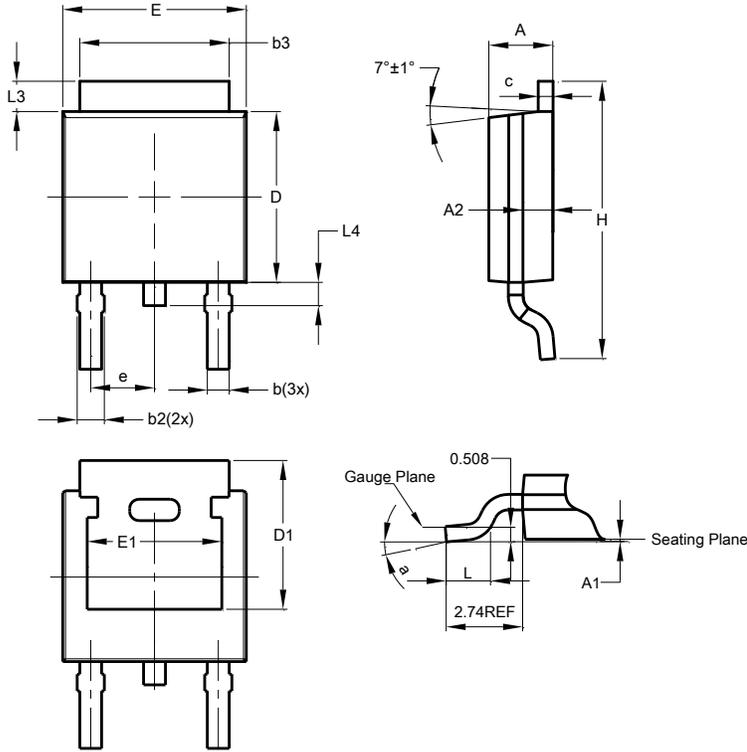


Switching time test circuit

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

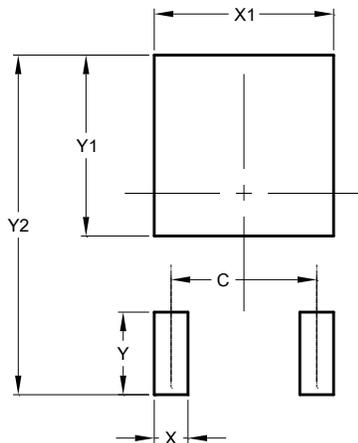


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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